SIPR-9332BE10 Thick Film Positive Photoresist

High Thermal Stability

The SIPR positive photoresist line has been formulated To give outstanding results in thicker photoresist Films. Highly vertical sidewalls are achieved using the SIPR one component positive photoresist. The SIPR one component positive photoresist, by binding sensitizer covalently to the resin, achieves high resolution with low optical absorption and high aspect ratio. SIPR positive photoresists have been formulated to meet the highly demanding applications of thin film Head manufacturing, high voltage ion implantation And aggressive etch processing.

DoF (3 μm L/S)605 mJ/cm^2

Dehydration Bake
150°C x 120 sec
HMDS Primed
23°C x 120 sec
Resist Apply
10.0 μm
P.B.
90°C x 120 sec
Exposure
NSR-1755i7A
NA=0.50, σ=0.6
PEB
None
Development
SSFD-238
(2.38% TMAH)
50 sec x 4 times

-3 μm

-2 μm

-1 μm

±0 μm

+1 μm

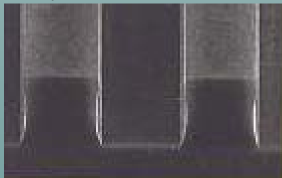
+2 μm

+3 μm

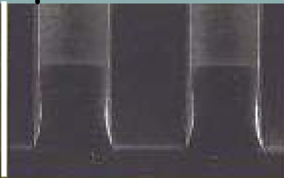
Linearity (10~1.5 μm)560 mJ/cm^2

Dehydration Bake
150°C x 120 sec
HMDS Primed
23°C x 120 sec
Resist Apply
10.0 μm
P.B.
90°C x 120 sec
Exposure
NSR-1755i7A
NA=0.50, σ=0.6
PEB
None
Development
SSFD-238
(2.38% TMAH) Puddle
50 sec x 3 times

10 μm



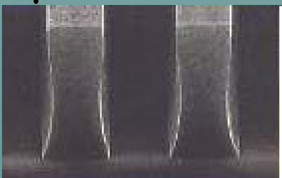
8 μm



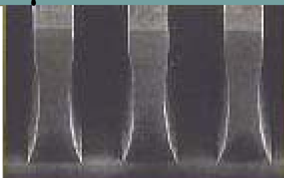
6 μm

5 μm

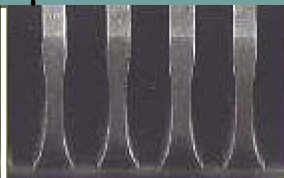
4 μm



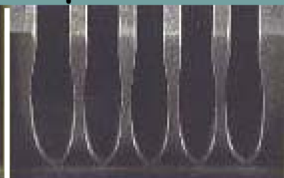
3 μm



2 μm

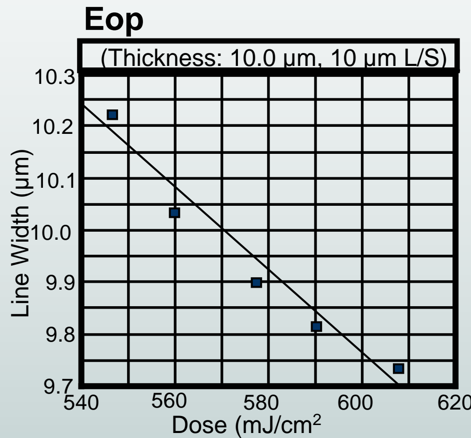


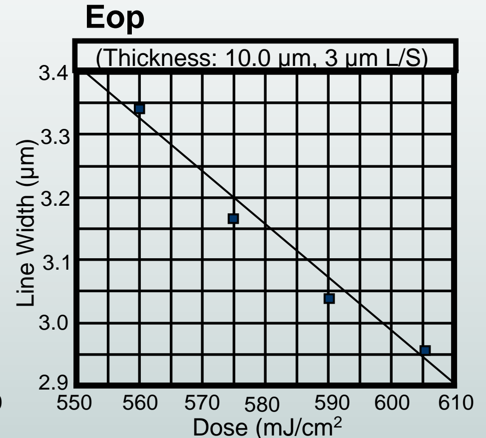
1.5 μm

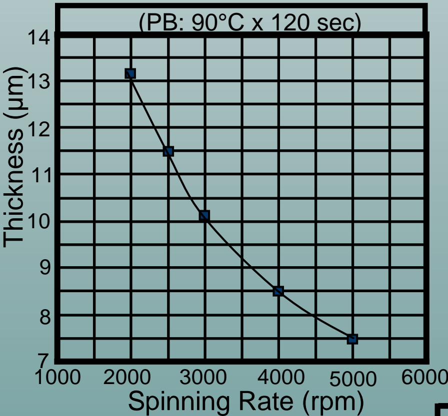


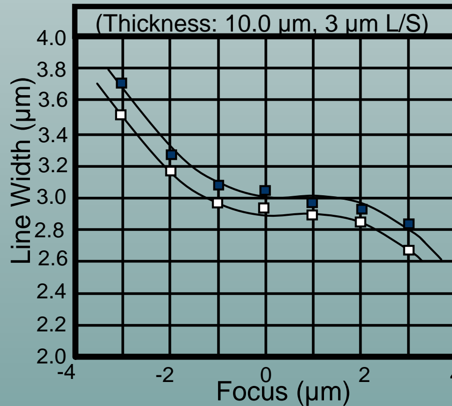
SIPR-9332BE10 Thick Film Positive Photoresist

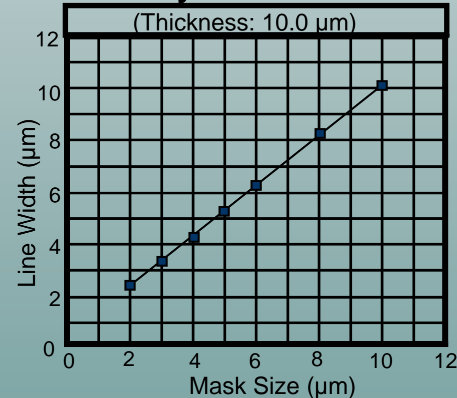
Dehydration Bake:
150°C x 120 sec
HMDS Primed:
23°C x 120 sec
Resist Apply:
10.0 µm
P.B.:
90°C x 120 sec
Exposure:
NSR-1755i7A
NA=0.50, σ=0.6
PEB:
without PEB
Development:
SSFD-238
(2.38% TMAH)
50 sec x 4 times











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